

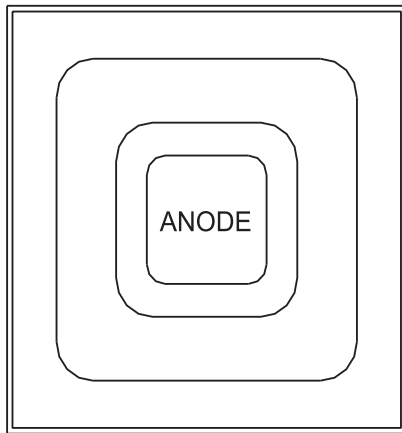
PROCESS CPD83V
Switching Diode
High Speed Switching Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	3.35 x 3.35 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 5 INCH WAFER

137,880

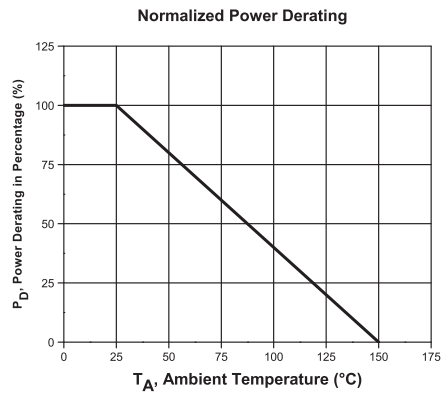
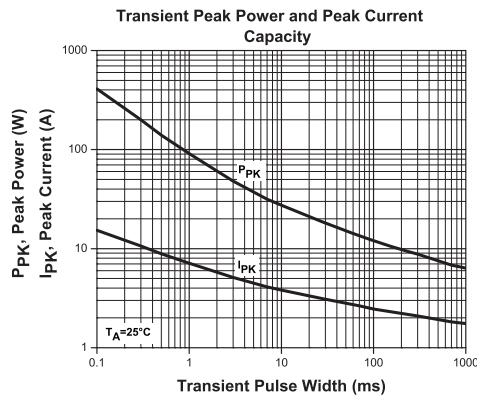
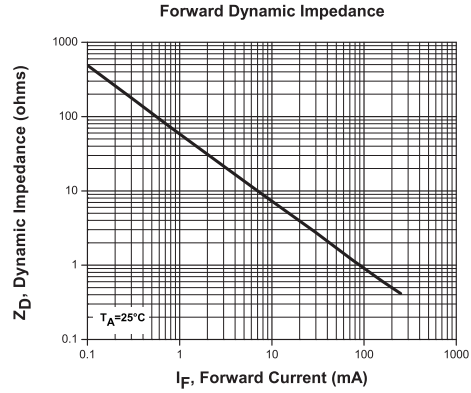
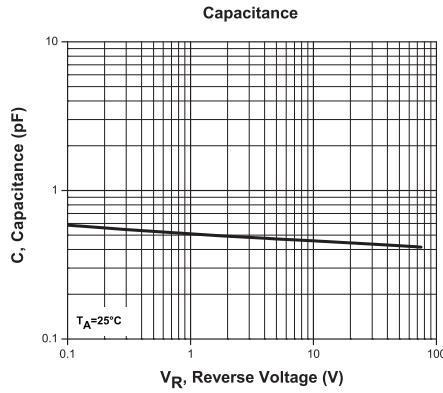
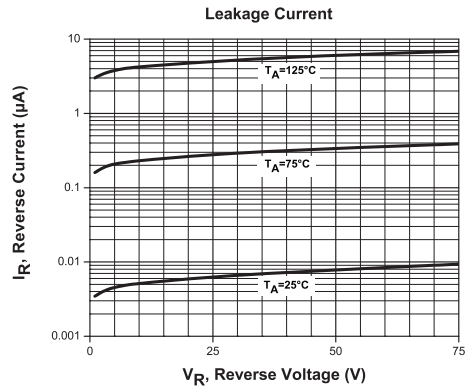
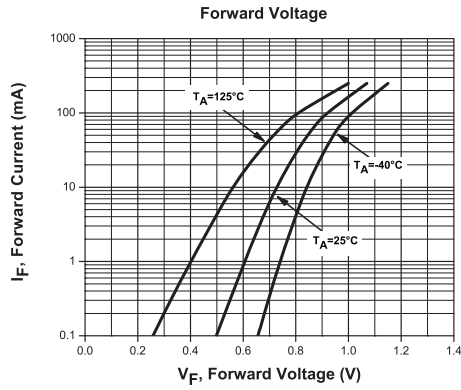
PRINCIPAL DEVICE TYPES

- CMPD914
- CMPD4448
- 1N914
- 1N914B
- 1N4148
- 1N4448
- 1N4154
- 1N4454
- CMPD2836
- CMPD2838
- CMPD7000

R5 (22-March 2010)

PROCESS CPD83V

Typical Electrical Characteristics



R5 (22-March 2010)